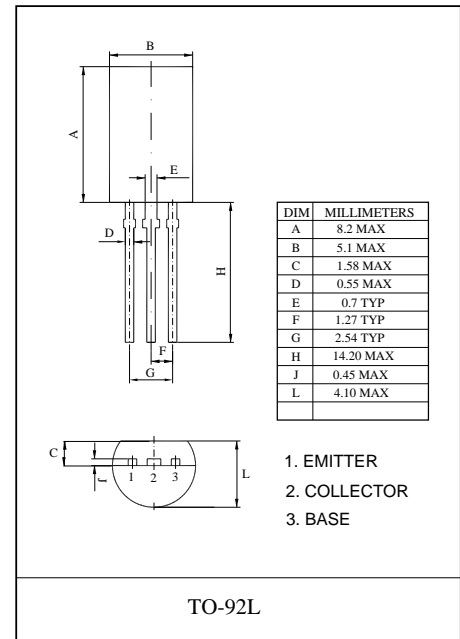


FTA1275 TRANSISTOR (PNP)

FEATURES

- High Voltage
- Large Continuous Collector Current Capability
- Complementary to FTC3228



MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	-160	V
V _{CEO}	Collector-Emitter Voltage	-160	V
V _{EBO}	Emitter-Base Voltage	-6	V
I _C	Collector Current	-1	A
P _C	Collector Power Dissipation	0.75	W
R _{θJA}	Thermal Resistance From Junction To Ambient	167	°C/W
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~+150	°C

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = -1mA, I _E =0	-160			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-10mA, I _B =0	-160			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-1mA, I _C =0	-6			V
Collector cut-off current	I _{CBO}	V _{CB} =-150V, I _E =0			-1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-6V, I _C =0			-1	μA
DC current gain	h _{FE}	V _{CE} =-5V, I _C =-200mA	60		320	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-500mA, I _B =-50mA			-1.5	V
Base-emitter voltage	V _{BE}	V _{CE} =-5V, I _C =-5mA	-0.45		-0.75	V
Collector output capacitance	C _{ob}	V _{CB} =-10V, I _E =0, f=1MHz			35	pF
Transition frequency	f _T	V _{CE} =-5V, I _C =-200mA	15			MHz

CLASSIFICATION OF h_{FE}

RANK	R	O	Y
RANGE	60-120	100-200	160-320